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Pressure Tuned Enhancement of Superconductivity and Change of Ground State Properties in $LaO_{0.5}F_{0.5}BiSe_2$ Single Crystals

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By using a hydrostatic pressure, we have successfully tuned the ground state and superconductivity in $LaO_{0.5}F_{0.5}BiSe_2$ single crystals. It is found that, with the increase of pressure, the original superconducting phase with $T_c \sim 3.5$ K can be tuned to a state with lower T_c, and then a new superconducting phase with $T_c \sim 6.5$ K emerges. Accompanied by this crossover, the ground state is switched from a semiconducting state to a metallic one. Accordingly, the normal state resistivity also shows a nonmonotonic change with the external pressure. Furthermore, by applying a magnetic field, the new superconducting state under pressure with $T_c \sim 6.5$ K is suppressed, and the normal state reveals a weak semiconducting feature again. These results illustrate a non-trivial relationship between the normal state property and superconductivity in this newly discovered superconducting system.

According to the theory of Bardeen-Cooper-Schrieffer (BCS), superconductivity is achieved by the quantum condensation of Cooper pairs which are formed by the electrons with opposite momentum near the Fermi surface. The ground state when superconductivity is removed is thus naturally believed to be metallic. In some unconventional superconductors, such as cuprate, iron pnictide/phosphide, heavy fermion and organic superconductors, this may not be true. Recently, the BiS_2-based superconductors whose structures are similar to the cuprates[1] and iron pnictides[2], have been discovered and formed a new superconducting (SC) family. Many new SC compounds with the BiS_2 layer have been found, including $Bi_4O_4S_3$[3–5], $REO_{1-x}F_xBiS_2$ (RE=La, Nd, Ce, Pr and Yb)[6–10], $Sr_{1-x}La_xFBiS_2$[11] and $La_{1-x}M_xOBiS_2$ (M=Ti, Zr, Hf and Th)[12], etc.. Among these compounds, the high pressure synthesized $LaO_{0.5}F_{0.5}BiS_2$ was reported to have a maximum $T_c \sim$ 10.6 K[6]. The basic band structure obtained by first principle calculations indicates the presence of strong Fermi surface nesting at the wave vector (π,π)[13–15] when the doping is close to x=0.5 in, for example, $LaO_{1-x}F_xBiS_2$. Quite often the superconductivity is accompanied by a normal state with a clear semiconducting behavior with unknown reasons[6–12]. In addition, possible triplet paring and weak topological superconductivity were suggested based on renormalization-group numerical calculation[16], but this mechanism is still much debated. Moreover, the experiments on the $NdO_{0.5}F_{0.5}BiS_2$ single crystals also reveal interesting discoveries concerning the SC mechanisms in this new system[17–21].

Through adjusting the lattice parameters and intimately the electronic band structure, high pressure has served as a very effective method, which can tune both the SC and normal state of superconductors. In this newly found BiS_2 family, high pressure has been recognized as an important tool to enhance both the superconductivity volume and transition temperatures except for $Bi_4O_4S_3$[22–28]. In particular, the SC transition temperature of $REO_{1-x}F_xBiS_2$ (RE=La, Ce, Nd, Pr)[22–24] and $Sr_{1-x}RE_xFBiS_2$ (RE = La, Ce, Nd, Pr, Sm)[25, 28] systems was enhanced tremendously by applying the hydrostatic pressure. Taking $LaO_{0.5}F_{0.5}BiS_2$ as an example, the T_c of the sample can be increased from about 2 K under ambient pressure to $\sim$ 10 K under 2 GPa[22]. And in the $Sr_{1-x}RE_xFBiS_2$ (R= Ce, Nd, Pr, Sm) system, the non-SC sample at ambient pressure can also be tuned to become a SC one with $T_c \sim$ 10 K under a pressure of 2.5 GPa[28]. To understand the role of high pressure, X-ray diffraction measurements under pressures have been performed on $LaO_{0.5}F_{0.5}BiS_2$ system and suggest a structural phase transition from a tetragonal phase ($P4/nmm$) to a monoclinic phase ($P21/m$) under pressures[27]. Very recently, a new superconductor $LaO_{0.5}F_{0.5}BiSe_2$ with the same structure as the $LaO_{0.5}F_{0.5}BiS_2$ was discovered with $T_c \sim 3.5$ K[29–31]. It was reported that the electronic structure and Fermi surface in these two compounds are quite similar[32]. Since the system now is selenium based, it is highly desired to do investigations on $BiSe_2$-based materials, better in form of single crystals. Furthermore it is curious to know how the high pressure influences the superconductivity and the ground state property in the $BiSe_2$-based superconductors.

Here, we report the successful growth of the $LaO_{0.5}F_{0.5}BiSe_2$ single crystals, and a systematic high-pressure study on two single crystals (hereafter named as Sample-1 and Sample-2). By increasing pressure, the ground state is switched from a semiconducting state to a metallic one, simultaneously the original SC $T_c \sim 3.5$ K (at ambient pressure) initially drops down to about 2 K and finally increases with pressure. As the pressure reaches about 1.2±0.2 GPa, a new SC phase with higher T_c appears. At about 2.17 GPa, the T_c of the new SC

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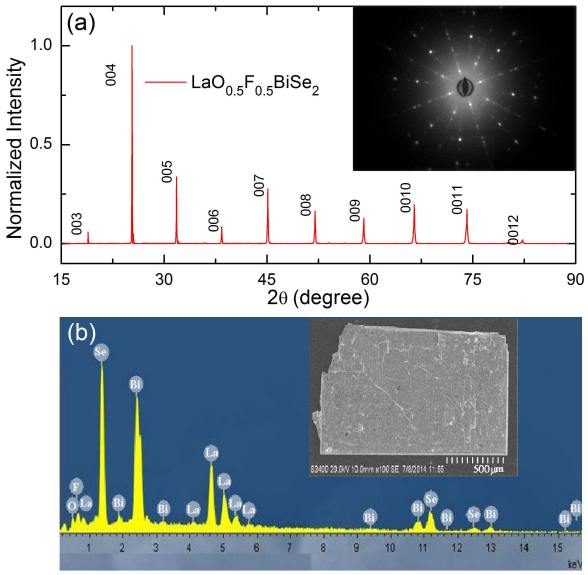

FIG. 1: (Color online) (a) X-ray diffraction pattern for a $LaO_{0.5}F_{0.5}BiSe_2$ single crystal. The inset shows the back Laue X-ray diffraction pattern of a $LaO_{0.5}F_{0.5}BiSe_2$ single crystal. (b) Energy Dispersive X-ray microanalysis spectrum taken on a $LaO_{0.5}F_{0.5}BiSe_2$ single crystal. The inset shows the SEM photograph of the crystal with typical dimensions of about $1.4 \times 0.7 \times 0.04$ mm^3.

phase reaches about 6.5 K. Accompanied with the change of SC transition temperatures, the normal state resistivity (ρ_n) decreases first and then increases with pressure. This non-monotonic pressure dependence of T_c and the normal state resistivity in the present $BiSe_2$-based system are very different from the BiS_2-based family. Furthermore, the SC phase with higher T_c can be suppressed by applying a magnetic field, and a weak semiconducting feature in the normal state emerges again when superconductivity is suppressed. All these results show the competing feature between superconductivity and the underlying ground state associated with the semiconducting behavior.

The $LaO_{0.5}F_{0.5}BiSe_2$ single crystals were grown by using flux method[18]. Powders of La_2O_3, LaF_3, Bi_2Se_3, Se and La scraps (all 99.9% purity) were mixed in stoichiometry as the formula of $LaO_{0.5}F_{0.5}BiSe_2$. The mixed powder was grounded together with CsCl/KCl powder (molar ratio CsCl : KCl : $LaO_{0.5}F_{0.5}BiSe_2$ = 12 : 8 : 1) and sealed in an evacuated quartz tube. Then it was heated up to 800°C for 50 hours followed by cooling down at a rate of 3°C/hour to 600°C. Single crystals with lateral sizes of about 1 mm were obtained by washing with water. X-ray diffraction (XRD) measurements were performed on a Bruker D8 Advanced diffractometer with the Cu-K_α radiation. DC magnetization measurements were carried out with a SQUID-VSM-7T (Quantum Design).

Measurements of resistivity under pressure were performed up to $\sim$ 2.3GPa on PPMS-16T (Quantum Design) by using HPC-33 Piston type pressure cell with the Quantum Design DC resistivity and AC transport options. The $LaO_{0.5}F_{0.5}BiSe_2$ single crystal with the standard four-probe method was immersed in pressure transmitting medium (Daphene 7373) in a Teflon cap.

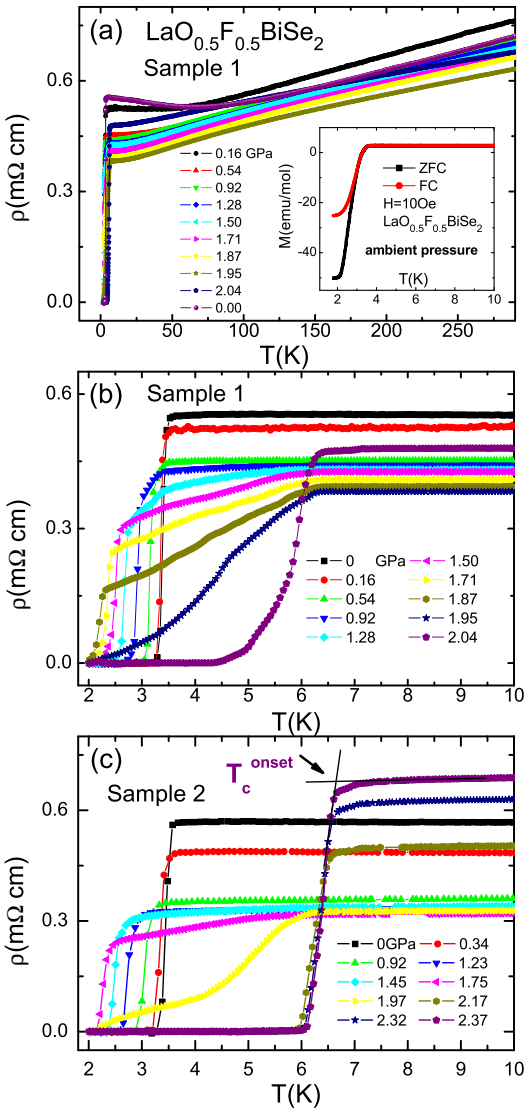

FIG. 2: (Color online) (a) Temperature dependence of resistivity for Sample-1 at various pressures in the temperature range 2 K to 300 K. The inset shows the magnetic susceptibility of a $LaO_{0.5}F_{0.5}BiSe_2$ single crystal in an applied field of 10 Oe ($\|$c-axis) under the ambient pressure. Both the magnetic susceptibility measured in zero-field-cooled (ZFC) and field-cooled (FC) modes are shown. (b) and (c) Enlarged views of the resistive transition in the temperature range 2 K to 10 K at various pressures for Sample-1 and Sample-2, respectively. The superconducting transitions are rather sharp at ambient and high pressures.

Hydrostatic pressures were generated by a BeCu/NiCrAl clamped piston-cylinder cell. The pressure upon the sample was determined by measuring the pressure-dependent T_c of a Sn sample with high purity.

In Fig. 1(a) we present the X-ray diffraction (XRD) pattern for the $LaO_{0.5}F_{0.5}BiSe_2$ single crystal. It's clear that only $(00l)$ reflections can be observed yielding a c-axis lattice constant $c = 14.05 \pm 0.03\mathring{A}$. The inset of Fig. 1(a) shows the Laue diffraction pattern of the $LaO_{0.5}F_{0.5}BiSe_2$ single crystal. Bright and symmetric spots can be clearly observed, indicating a good crystallinity. Energy dispersive X-ray spectrum (EDS) measurements were performed at an accelerating voltage of 20kV and working distance of 10 millimeters by a scanning electron microscope (Hitachi Co.,Ltd.). One set of the EDS result on $LaO_{0.5}F_{0.5}BiSe_2$ single crystal is shown in Fig. 1(b), and the composition of the single crystal can be roughly expressed as $LaO_yF_{0.48}Bi_{0.95}Se_{1.89}$. The atomic ratio is close to the nominal composition except for oxygen which can not be obtained accurately by the EDS measurement.

The temperature dependence of resistivity for the $LaO_{0.5}F_{0.5}BiSe_2$ single crystal (Sample-1) at various pressures with temperature ranging from 2 K to 300 K is illustrated in Fig. 2(a). The inset of Fig. 2(a) shows the temperature dependent magnetic susceptibility at ambient pressure under a magnetic field of 10 Oe, and a sharp SC transition is observed at about 3.5 K. An estimate on the Meissner screening volume through the magnetic susceptibility measured in the zero-field-cooled (ZFC) mode reveals a high superconducting volume. For Sample-1, we were not managed to measure the sample at a pressure higher than 2.04 GPa. As shown in Fig. 2(a), at ambient pressure the normal state resistivity shows a semiconducting behavior. This semiconducting behavior can be suppressed under a small pressure and turns to be a metallic one at about 0.54 GPa. With further increase of pressure, the metallic behavior maintains until the maximum pressure. This semiconducting to metallic transition with pressure has been noticed in $Sr_{1-x}RE_xFBiS_2$ (R= La, Ce, Nd, Pr, Sm) systems[25, 28]. In the case of $Sr_{0.5}La_{0.5}FBiS_2$ polycrystalline sample, the semiconductor-metal transition was considered as coming from the change of F-Sr/La-F bond angle along with inter-atomic distances[25]. Interestingly, the semiconductor-metal transition under pressure for $CeO_{0.5}F_{0.5}BiS_2$ system has been proposed according to the first-principle calculations[33], but the transition was not observed in previous reports of experiment[23, 26]. In particular, for $LaO_{0.5}F_{0.5}BiS_2$ polycrystalline samples, the normal state resistivity decreases monotonically with increasing pressure, but it still exhibits semiconducting behavior under a very high pressure (18 GPa)[27].

In Fig. 2(b) and (c), we present enlarged views of SC transitions at low temperatures under various pressures for Sample-1 and Sample-2, respectively. Both samples exhibit very similar behavior. As one can see, the variation of both the SC transition temperature and normal state resistivity upon the external pressure are non-monotonic. The original $T_c \sim 3.5$ K (at ambient pressure) gradually drops down with increasing pressure and becomes below 2 K at about 1.95 GPa. At the same time, a high T_c phase gradually emerges starting from about 1.2±0.2 GPa and enhances continuously with increasing pressure. It seems that the high T_c phase with $T_c = 6.5$K coexists with the low T_c phase in the range from 1.2±0.2 GPa to about 1.95 GPa. With further increase of pressure, zero resistance corresponding to the high T_c phase appears above 2 K and the SC transition becomes sharper at higher pressures. A similar behavior under pressure has been observed in some strongly correlated electronic systems, such as heavy fermion[34], organic systems[35] and iron chalcogenides[36]. In previous high pressure studies on BiS_2-based superconductors, the T_c monotonically increases with the pressure without showing the coexistence of two transient phases. This indicates the distinction between our present $BiSe_2$-based superconductors and the earlier studied BiS_2-based systems. For Sample-1 we were not managed to measure the resistivity beyond 2.04 GPa. Two samples are from the same batch. One can see that the resistive transitions below 2.04 GPa are quite similar to each other.

It is worth noting that the normal state resistivity presents a non-monotonic dependence on applied pressure. As shown in Fig. 2(b) and (c), the normal state resistivity just above the SC transition temperature gradually decreases with increasing pressure till about 1.95 GPa. Surprisingly, above the threshold pressure, the normal state resistivity begins to increase remarkably with increasing pressure. It is clear that this qualitative behavior is closely related to the pressure-dependent T_c, as we addressed below.

Fig. 3(a) and 3(b) present the phase diagram of T_c^{onset} versus pressure and pressure-dependent resistivity (8K), respectively. Here, the pressure for the absence of the second transition (about 1.95GPa) is defined as the critical one (P_c). Fig. 3(a) and 3(b) clearly reveal two distinct SC phases: the low T_c SC phase below P_c and the high T_c SC phase above P_c. In the low T_c SC phase region, both T_c and the normal state resistivity are suppressed with increasing pressure. On the contrary, in the high T_c SC phase, T_c is slightly enhanced and the normal state resistivity increases remarkably with raising pressure. In $LaO_{0.5}F_{0.5}BiS_2$ polycrystalline samples, a structural phase transition from a tetragonal phase ($P4/nmm$) to a monoclinic phase ($P21/m$) has been suggested by high-pressure X-ray diffraction measurements. And a high T_c value of 10.7K in the high-pressure regime appears in the monoclinic structure[27]. Therefore, considering the very weak change of the transition temperature of the high T_c phase, and taking a comparison between $LaO_{0.5}F_{0.5}BiS_2$ and $LaO_{0.5}F_{0.5}BiSe_2$, we believe that there are two distinct SC phases in our $LaO_{0.5}F_{0.5}BiSe_2$ single crystals in the intermediate pressure region (1.2±0.2 to $\sim$ 1.95 GPa). At a high pressure, all the phase becomes super-

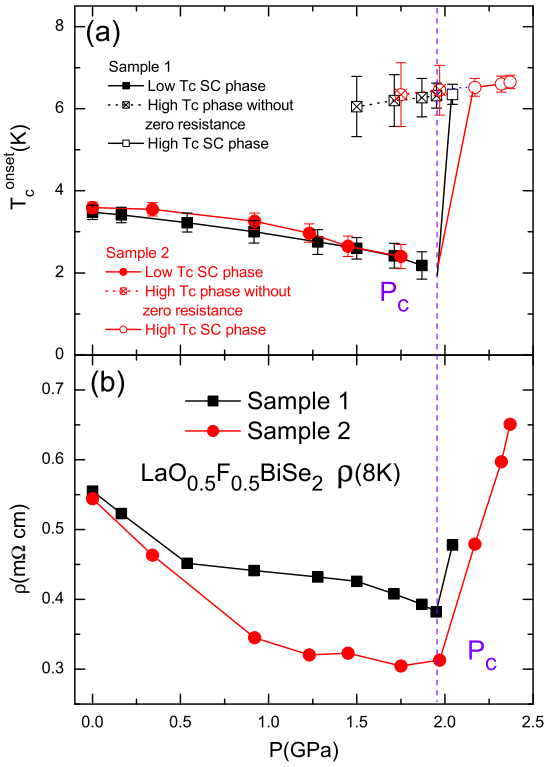

FIG. 3: (Color online)(a) Phase diagram of T_c^{onset} versus pressure for the two $LaO_{0.5}F_{0.5}BiSe_2$ single crystals investigated here. The dark and red symbols represent the T_c^{onset} of Sample-1 and Sample-2, respectively. The filled symbols stand for the low T_c phase, the open and crossed symbols stand for the high T_c phase with and without zero resistance, respectively. (b) Resistivity at 8 K in the normal state at various pressures for Sample-1 (filled squares) and Sample-2 (filled circles) .

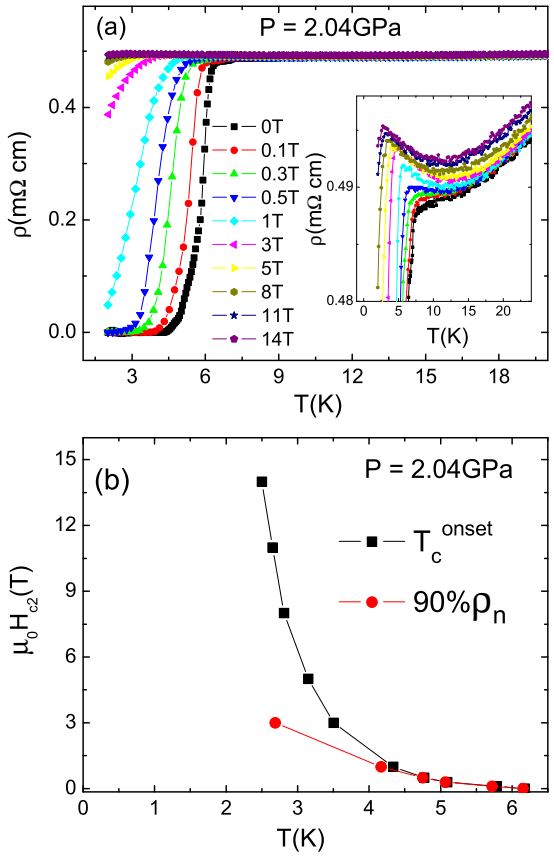

FIG. 4: (Color online) (a) Temperature dependence of resistivity for Sample-1 under a pressure of 2.04 GPa at various magnetic fields. The inset shows the enlarged view of a weak semiconducting feature in the normal state under high magnetic fields. (b) Upper critical field determined by T_c^{onset} and 90% normal state resistivity ρ_n.

conductive with $T_c \sim 6.5$ K. The transition from the low T_c phase to the high T_c one could be induced by the structural transition, which needs to be further checked.

In Fig. 4(a), we present the temperature dependent resistivity under magnetic field up to 14 T at 2.04 GPa ($T_c \sim 6.3$K). The upper critical field H_{c2} versus T_c is displayed in Fig. 4(b). We use different criterions of 90%ρ_n and T_c^{onset} (determined using the crossing point shown in Fig. 2(c)) to determine the H_{c2}. The upper critical field at zero temperature can be estimated by using the Werthamer-Helfand-Hohenberg (WHH) formula[37] $H_{c2} = -0.69T_c[dH_{c2}/dT]_{T_c}$, and the estimated $H_{c2}(0)$ is about 35 T for T_c^{onset}. The inset of Fig. 4(a) shows the enlarged view of superconducting transitions as in the main panel. As shown in the inset, the SC is very robust and keeps presence above 2 K when the field is up to 14 T. That could be induced by the fact that the applied field was approximately parallel to *ab* plane of the single crystal in the pressure cell during the measurement, and a large anisotropy has been discovered in $LaO_{0.5}F_{0.5}BiSe_2$ single crystals[30]. An interesting phenomenon is that a weak semiconducting behavior re-emerges when the superconductivity is suppressed under a high magnetic field. A similar behavior was observed in $NdO_{0.5}F_{0.5}BiS_2$ single crystals[18]. This phenomenon may be related to the semiconducting behavior of the sample at an ambient pressure, although it seems that the low T_c phase does not show up here. The semiconducting ground states for either the low T_c phase at an ambient pressure, or the one with high T_c superconductivity under a high pressure but suppressed with a high magnetic field, may be caused by the same reason, both point to the competition of superconductivity with a tendency which underlines the semiconducting behavior.

In summary, we have successfully tuned the ground state and superconductivity in $LaO_{0.5}F_{0.5}BiSe_2$ single crystals through a hydrostatic pressure. The ground

state is switched from a semiconducting state to a metallic one with increasing pressure. Moreover, the original SC phase with $T_c \sim 3.5$ K can be tuned to a new SC state with $T_c \sim 6.5$ K. In the low T_c SC phase region, both T_c and the normal state resistivity are suppressed with increasing pressure. On the contrary, in the high T_c SC phase, superconductivity is enhanced and the normal state resistivity increases remarkably with increasing pressure. Moreover, a weak semiconducting behavior reemerges when the superconductivity under a high pressure is suppressed under magnetic field. These results illustrate a non-trivial relationship between the normal state property and superconductivity. Further theoretical and detailed structure investigations are highly desired to clarify the new high T_c SC phase under a high pressure.

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